

	L #	Hits	Search Text	DBs	Time Stamp
1	L1	512	(semiconductor near3 laser) and aperture and (conduct\$ near3 (layer region plane))	USPAT; EPO; JPO; DERWENT	2002/03/26 18:44
2	L2	45	1 and ("near" near2 field)	USPAT; EPO; JPO; DERWENT	2002/03/26 18:47
3	L7	146	1 and (mesa protrusion ridge)	USPAT; EPO; JPO; DERWENT	2002/03/26 18:48
4	L12	115	7 not 2	USPAT; EPO; JPO; DERWENT	2002/03/26 19:27
5	L17	9288	xerox.as. and laser	USPAT; EPO; JPO; DERWENT	2002/03/26 20:03
6	L22	1666	17 and (semiconductor with laser)	USPAT; EPO; JPO; DERWENT	2002/03/26 20:04
7	L27	176	22 and aperture	USPAT; EPO; JPO; DERWENT	2002/03/26 20:04
8	L37	17	27 and 32	USPAT; EPO; JPO; DERWENT	2002/03/26 20:13
9	L32	171	17 and (thornton chua treat shi).in.	USPAT; EPO; JPO; DERWENT	2002/03/26 20:05
10	L42	159	27 not 32	USPAT; EPO; JPO; DERWENT	2002/03/26 20:14